

PUMD16-Q

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 22 k Ω , R2 = 47 k Ω

8 March 2023

Product data sheet

1. General description

NPN/PNP double Resistor-Equipped Transistor (RET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: PUMH16 PNP/PNP complement: PUMB16

2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplified circuit design
- · Reduces component count
- Reduces pick and place costs
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- Low current peripheral driver
- Controlling IC inputs
- · Replacement of general purpose transistors in digital applications

4. Quick reference data

Table 1. Quick reference data

Table 1. Quick reletellee data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	or				'	'	
V_{CEO}	collector-emitter voltage	open base	[1]	-	-	50	V
Io	output current		[1]	-	-	100	mA
R1	bias resistor 1 (input)		[2]	15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		[2]	1.7	2.1	2.6	

- [1] For the PNP transistor with negative polarity.
- [2] See section "Test information" for resistor calculation and test conditions.



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1	D. D. D.	
3	O2	output (collector) TR2	6 5 4	R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2	0	TR1 R2 R1
6	01	output (collector) TR1	☐1 ☐2 ☐3 TSSOP6 (SOT363)	GND1 I1 O2
				006aaa143

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PUMD16-Q		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	<u>SOT363</u>		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PUMD16-Q	D1%

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transisto	or					
V _{CBO}	collector-base voltage	open emitter	[1]	-	50	V
V_{CEO}	collector-emitter voltage	open base	[1]	-	50	V
V _{EBO}	emitter-base voltage	open collector	[1]	-	5	V
V _I	input voltage	TR1 (NPN)		-7	40	V
		TR2 (PNP)		-40	7	V
Io	output current		[1]	-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	200	mW
Per device						
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	300	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

^{1]} For the PNP transistor with negative polarity.

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W
Per device	Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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10. Characteristics

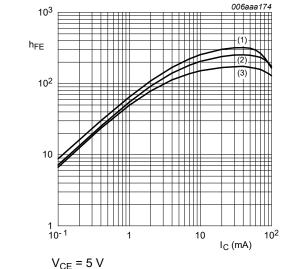
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or						
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	[1]	50	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	[1]	50	-	-	V
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	[1]	-	-	100	nA
I _{CEO}	collector-emitter cut-off	V _{CE} = 30 V; I _B = 0 A; T _{amb} = 25 °C	[1]	-	-	100	nA
current	current	V _{CE} = 30 V; I _B = 0 A; T _j = 150 °C	[1]	-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	[1]	-	-	120	μΑ
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 5 mA; T _{amb} = 25 °C	[1]	80	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	-	-	150	mV
$V_{I(off)}$	off-state input voltage	V _{CE} = 5 V; I _C = 100 μA; T _{amb} = 25 °C	[1]	-	8.0	0.5	V
V _{I(on)}	on-state input voltage	V _{CE} = 0.3 V; I _C = 2 mA; T _{amb} = 25 °C	[1]	2	1.1	-	V
R1	bias resistor 1 (input)		[2]	15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		[2]	1.7	2.1	2.6	
TR1 (NPN)							
C _c	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	-	2.5	pF
TR2 (PNP)	·						1
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C		-	-	3	pF

^[1] For the PNP transistor with negative polarity.

^[2] See section "Test information" for resistor calculation and test conditions.

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 22 k Ω , R2 = 47 k Ω



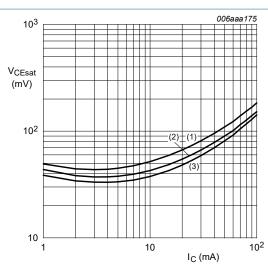
$$V_{CE} = 5 V$$

(1) $T_{amb} = 100 °C$

(2)
$$T_{amb} = 100^{\circ} C$$

(2) $T_{amb} = 25^{\circ} C$
(3) $T_{amb} = -40^{\circ} C$

TR1 (NPN): DC current gain as a function of Fig. 1. collector current; typical values



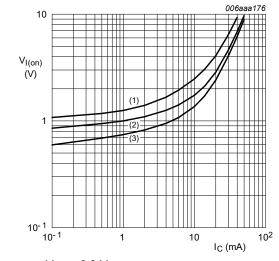
$$I_{\rm C}/I_{\rm B} = 20$$

$$(1) T_{amb} = 100 °C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(1) T_{amb} = 100 °C (2) T_{amb} = 25 °C (3) T_{amb} = -40 °C

Fig. 2. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



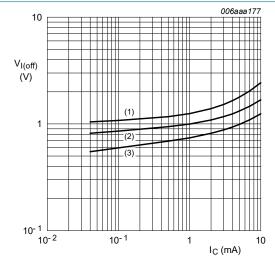
$$V_{CE}$$
 = 0.3 V

$$(1) T_{amb} = -40 °C$$

$$(2) T_{amb} = 25 °C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 3. TR1 (NPN): On-state input voltage as a function | Fig. 4. of collector current; typical values



$$V_{CE} = 5 V$$

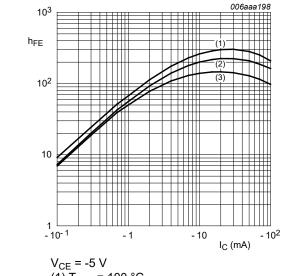
(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

TR1 (NPN): Off-state input voltage as a function of collector current; typical values

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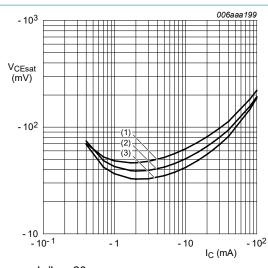


$$V_{CE} = -5 V$$

$$(1) I_{amb} = 100 °($$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

TR2 (PNP): DC current gain as a function of Fig. 5. collector current; typical values

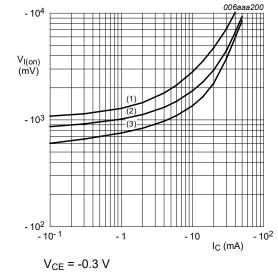


$$I_{\rm C}/I_{\rm B}=20$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 6. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

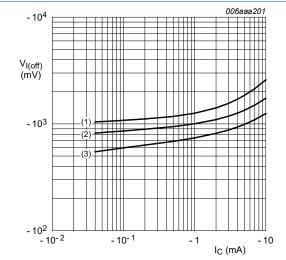


$$(1) T_{amb} = -40 °C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = 100 °C$$

Fig. 7. TR2 (PNP): On-state input voltage as a function | Fig. 8. of collector current; typical values



$$V_{CE} = -5 V$$

$$(1) T_{amb} = -40 °C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

TR2 (PNP): Off-state input voltage as a function of collector current; typical values

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 22 k Ω , R2 = 47 k Ω

11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

Resistor calculation

· Calculation of bias resistor 1 (R1)

$$R_{I} = \frac{V(I_{2}) - V(I_{I})}{I_{2} - I_{I}}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I4) - V(I3)}{R1 \cdot (I4 - I3)} - 1$$

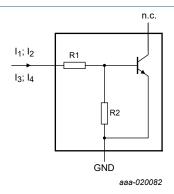


Fig. 9. NPN transistor: Resistor test circuit

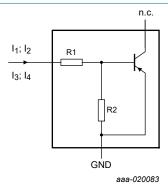


Fig. 10. PNP transistor: Resistor test circuit

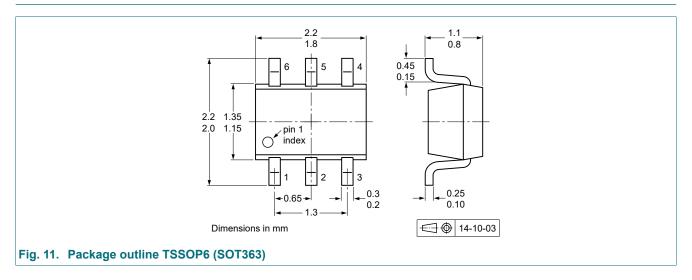
Resistor test conditions

Table 8. Resistor test conditions

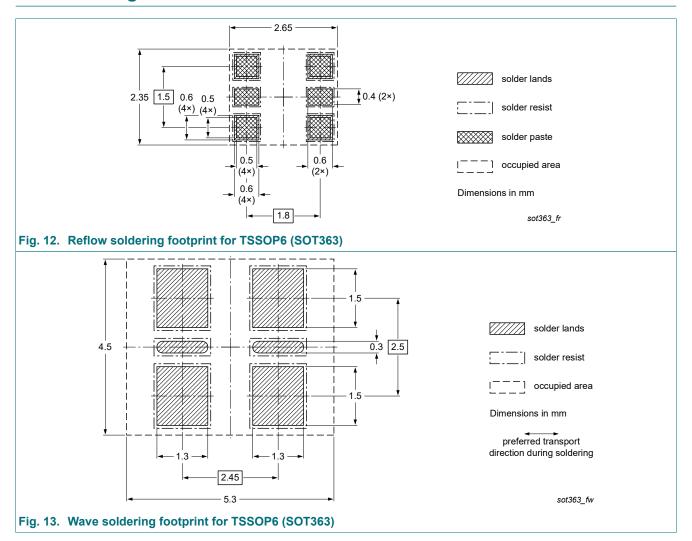
PUMD16-Q	R1 (kΩ)	R2 (kΩ)	Test conditions				
			I ₁	l ₂	I ₃	14	
TR1 (NPN)	22	47	55 μΑ	105 μΑ	-55 μΑ	-105 μA	
TR2 (PNP)	22	47	-55 μA	-105 μA	55 μΑ	105 μΑ	

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12. Package outline



13. Soldering



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50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 22 k Ω , R2 = 47 k Ω

14. Revision history

Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PUMD16-Q v.1	20230308	Product data sheet	-	-

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 22 k Ω , R2 = 47 k Ω

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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